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### FDS8884

# N-Channel PowerTrench® MOSFET

**30V**, **8.5A**, **23m**Ω

### **General Descriptions**

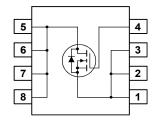
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $r_{DS(on)}$  and fast switching speed.



#### **Features**

- Max  $r_{DS(on)} = 23m\Omega$  at  $V_{GS} = 10V$ ,  $I_D = 8.5A$
- Max  $r_{DS(on)} = 30m\Omega$  at  $V_{GS} = 4.5V$ ,  $I_D = 7.5A$
- Low gate charge
- 100% R<sub>G</sub> Tested
- RoHS Compliant





### **MOSFET Maximum Ratings** $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	±20	V
	Drain Current Continuous (Note 1a)	8.5	Α
ID	Pulsed	40	Α
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 2)	32	mJ
В	Power dissipation	2.5	W
$P_{D}$	Derate above 25°C	20	mW/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	-55 to 150	°C

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Case	(Note 1)	25	°C/W

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS8884	FDS8884	SO-8	330mm	12mm	2500 units

## **Electrical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu$ A, referenced to $25^{\circ}$ C		23		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24V$ $V_{GS} = 0V$ $T_{J} = 125^{\circ}C$			1 250	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20V$			±100	nA

#### On Characteristics (Note 3)

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.2	1.7	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25°C		-4.9		mV/°C
		$V_{GS} = 10V, I_D = 8.5A,$		19	23	
r Drain to Source On Begintance	Drain to Source On Resistance	$V_{GS} = 4.5V$ , $I_{D} = 7.5A$ ,		23	30	mΩ
r <sub>DS(on)</sub>	Brain to course on resistance	$V_{GS} = 10V, I_D = 8.5A,$ $T_J = 125^{\circ}C$		26	32	11152

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 45V V 0V	475	635	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz	100	135	рF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 – 1101112	65	100	pF
$R_G$	Gate Resistance	f = 1MHz	0.9	1.6	Ω

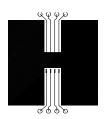
#### **Switching Characteristics (Note 3)**

t <sub>d(on)</sub>	Turn-On Delay Time		5	10	ns
t <sub>r</sub>	Rise Time	$V_{DD} = 15V, I_D = 8.5A$ $V_{GS} = 10V, R_{GS} = 33\Omega$	9	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 10V, H <sub>GS</sub> = 3322	42	68	ns
t <sub>f</sub>	Fall Time		21	34	ns
Qg	Total Gate Charge	$V_{DS} = 15V, V_{GS} = 10V$ $I_{D} = 8.5A$	9.2	13	nC
$Q_g$	Total Gate Charge	$V_{DS} = 15V, V_{GS} = 5V$	5.0	7	nC
$Q_{gs}$	Gate to Source Gate Charge	I <sub>D</sub> = 8.5A	1.5		nC
$Q_{gd}$	Gate to Drain Charge		2.0		nC

#### **Drain-Source Diode Characteristics**

V <sub>SD</sub> Source to Drain Diode Voltage		I <sub>SD</sub> = 8.5A	0.9	1.25	V
V <sub>SD</sub>	Source to Diairi Diode Voltage	$I_{SD} = 2.1A$	8.0	1.0	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 8.5A, di/dt = 100A/μs		33	ns
$Q_{rr}$	Reverse Recovery Charge			20	nC

<sup>13</sup> R<sub>8,IA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>8,IC</sub> is guaranteed by design while R<sub>8CA</sub> is determined by the user's board design.



a) 50°C/W when mounted on a 1 in2 pad of 2 oz copper



b) 105°C/W when mounted on a .04 in<sup>2</sup> pad of 2 oz copper



c) 125°C/W when mounted on a minimun pad

Scale 1: 1 on letter size paper

2: Starting  $T_J=25^{\circ}C$ , L = 1mH, I<sub>AS</sub> = 8A, V<sub>DD</sub> = 27V, V<sub>GS</sub> = 10V. 3: Pulse Test:Pulse Width <300 $\mu$ S, Duty Cycle <2%.



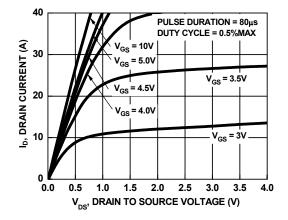
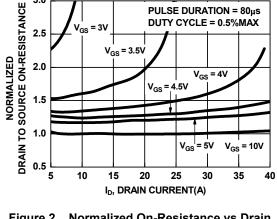


Figure 1. On Region Characteristics



3.0

Figure 2. Normalized On-Resistance vs Drain current and Gate Voltage

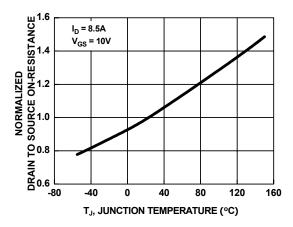


Figure 3. Normalized On Resistance vs Junction Temperature

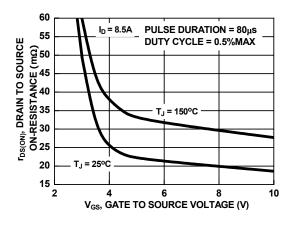


Figure 4. On-Resistance vs Gate to Source Voltage

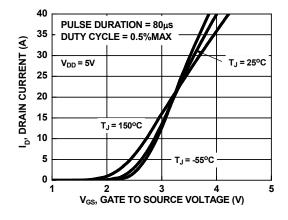


Figure 5. Transfer Characteristics

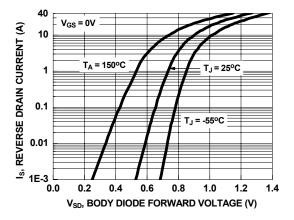


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

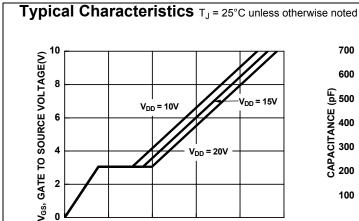


Figure 7. Gate Charge Characteristics

6

Q<sub>g</sub>, GATE CHARGE(nC)

8

10

0

2

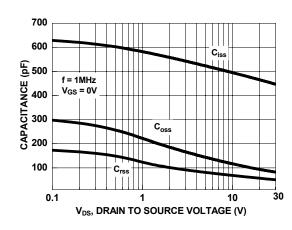


Figure 8. Capacitance vs Drain to Source Voltage

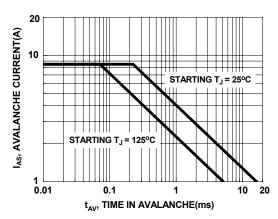


Figure 9. Unclamped Inductive Switching Capability

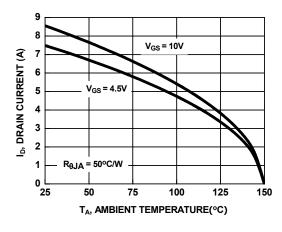


Figure 10. Maximum Continuous Drain Current vs **Ambient Temperature** 

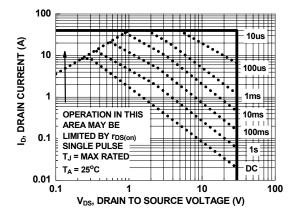


Figure 11. Forward Bias Safe Operating Area

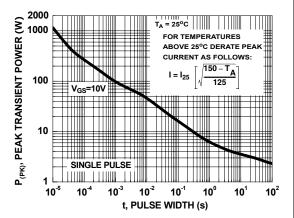


Figure 12. Single Pulse Maximum Power Dissipation

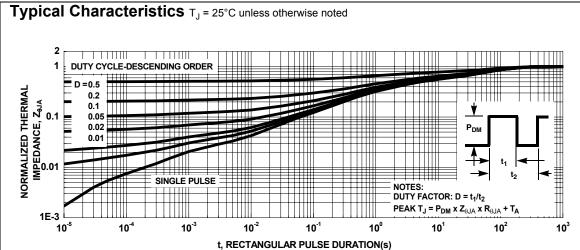


Figure 13. Transient Thermal Response Curve

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